

# Shyam Bharadwaj

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

14  
papers

179  
citations

6  
h-index

13  
g-index

14  
ext. papers

230  
ext. citations

3  
avg, IF

3.01  
L-index

#	Paper	IF	Citations
14	Enhanced efficiency in bottom tunnel junction InGaN blue LEDs <b>2021</b> ,		3
13	Dislocation and indium droplet related emission inhomogeneities in InGaN LEDs. <i>Journal Physics D: Applied Physics</i> , <b>2021</b> , 54, 495106	3	1
12	Inactivation of Listeria and E. coli by Deep-UV LED: effect of substrate conditions on inactivation kinetics. <i>Scientific Reports</i> , <b>2020</b> , 10, 3411	4.9	18
11	Monolithically p-down nitride laser diodes and LEDs obtained by MBE using buried tunnel junction design <b>2020</b> ,		2
10	Enhanced injection efficiency and light output in bottom tunnel-junction light-emitting diodes. <i>Optics Express</i> , <b>2020</b> , 28, 4489-4500	3.3	12
9	GaN/AlN quantum-disk nanorod 280 nm deep ultraviolet light emitting diodes by molecular beam epitaxy. <i>Optics Letters</i> , <b>2020</b> , 45, 121	3	21
8	Nitride LEDs and Lasers with Buried Tunnel Junctions. <i>ECS Journal of Solid State Science and Technology</i> , <b>2020</b> , 9, 015018	2	5
7	Bottom tunnel junction blue light-emitting field-effect transistors. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 031107	3.4	2
6	Light-emitting diodes with AlN polarization-induced buried tunnel junctions: A second look. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 061104	3.4	5
5	Polarization control in nitride quantum well light emitters enabled by bottom tunnel-junctions. <i>Journal of Applied Physics</i> , <b>2019</b> , 125, 203104	2.5	14
4	Blue (In,Ga)N light-emitting diodes with buried n <sup>+</sup> p <sup>+</sup> tunnel junctions by plasma-assisted molecular beam epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, 060914	1.4	3
3	Bandgap narrowing and Mott transition in Si-doped Al <sub>0.7</sub> Ga <sub>0.3</sub> N. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 113501	3.4	6
2	Efficient InGaN p-Contacts for deep-UV Light Emitting Diodes <b>2019</b> ,		2
1	MBE-grown 232-270 nm deep-UV LEDs using monolayer thin binary GaN/AlN quantum heterostructures. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 041108	3.4	85